Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"5458518".pn.	US-PGPUB; USPAT	OR	OFF	2005/01/21 14:49
L2	12	("5228878" | "5389026").PN. OR ("5458518").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/21 14:52
L3	42	("3665241" | "3755704" | "3812559" | "3954523" | "4016017" | "4266233" | "4652467" | "4857161" | "4987101" | "5103288" | "5142184" | "5186670" | "5194780" | "5229331" | "5259799" | "5358908" | "5372973" | "5430300" | "5458518" | "5470801" | "5473222" | "5483067" | "5529524" | "5569058" | "5578896" | "5585301" | "5597444" | "5653619" | "5663608" | "5684356" | "5712534" | "5793154" | "5804910" | "5853492" | "5869169" | "5898258" | "6028322" | "6232705" | "6251470" | "6255156" | "6277765" | "6333215").PN. OR ("6835111").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/21 14:59
L4	16	3 and (porous porosity pores)	US-PGPUB; USPAT	OR	OFF	2005/01/21 16:17
L15	12	("5228878" | "5389026").PN. OR ("5458518").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/21 19:03
L16	1	"20040189175"	US-PGPUB; USPAT	OR	OFF	2005/01/21 20:02
L17	2	((polishing with (mechanic$3 chemical$3) with silicon) same planariz$6) and 445/24.ccls.	US-PGPUB; USPAT	OR	OFF	2005/01/21 20:04
S1	86	(445/24,49-51.ccls. 438/20.ccls.) and (electron near3 (emitter emission emissive emitting)) and (tip micro$tip micro$point acicular cone) and silicon and (porosity porous pore)	US-PGPUB; USPAT	OR	ON	2005/01/21 14:48
S2	12	("3970887" | "4144636" | "4252833" | "4338164" | "4380865" | "4801380" | "5141459" | "5173634" | "5191217" | "5203731" | "5219310" | "5302238").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/14 18:50

S3	64	(445/24,49-51.ccls. 438/20.ccls.) and (electron near3 (emitter emission emissive emitting)) and (tip micro$tip micro$point acicular cone) and silicon and (porosity porous pore) and (poly$crystal$5 crystal$5)	US-PGPUB; USPAT	OR	ON	2004/12/14 18:51
S4	0	(electron near3 (emitter emission emissive emitting)) and (tip micro$tip micro$point acicular cone) and silicon and (porosity porous pore) and (poly$crystal$5 crystal$5)	EPO; JPO; DERWENT	OR	ON	2004/12/14 18:52
S5	77	(electron near3 (emitter emission emissive emitting)) and silicon and (porosity porous pore) and (poly$crystal$5 crystal$5)	EPO; JPO; DERWENT	OR	ON	2004/12/14 18:52
S6	1096	("445"/$.ccls. "438"/$.ccls.) and (silicon with (poly$crystal$5 crystal$5)) and (silicon with (pore porous porosity))	US-PGPUB; USPAT	OR	ON	2004/12/14 19:15
S7	705	("445"/$.ccls. "438"/$.ccls.) and (silicon with (poly$crystal$5 crystal$5)) and (silicon with (pore porous porosity)) and oxidiz$3	US-PGPUB; USPAT	OR	ON	2004/12/14 19:16
S8	274	("445"/$.ccls. "438"/$.ccls.) and (silicon with (poly$crystal$5 crystal$5)) and (silicon with (pore porous porosity)) and oxidiz$3 and anodiz$3	US-PGPUB; USPAT	OR	ON	2004/12/14 19:22
S9	20	("445"/$.ccls. "438"/$.ccls.) and (silicon with (poly$crystal$5 crystal$5)) and (silicon with (pore porous porosity)) and oxidiz$3 and anodiz$3 and ((field electron) near3 (emission emitter emissive emitting))	US-PGPUB; USPAT	OR	ON	2004/12/14 19:26
S10	45	(silicon with (poly$crystal$5 crystal$5)) and (silicon with (pore porous porosity)) and oxidiz$3 and anodiz$3 and ((field electron) near3 (emission emitter emissive emitting))	US-PGPUB; USPAT	OR	ON	2004/12/14 19:27
S11	8	(silicon with (poly$crystal$5 crystal$5)) and (silicon with (pore porous porosity)) and oxidiz$3 and anodiz$3 and ((field electron) near3 (emission emitter emissive emitting))	EPO; JPO; DERWENT	OR	ON	2004/12/14 19:26
S12	25	S10 not S9	US-PGPUB; USPAT	OR	ON	2004/12/15 17:23

S13	1	"6464853".pn.	US-PGPUB; USPAT	OR	ON	2004/12/15 17:18
S14	136	(silicon with (pore porosity porous)) and (oxidat$3 oxidiz$3) and (anodiz$3 anodization) and (dielectric insulator insulat$3 isolat$3) and (((field electron) near3 (emission emissive emitting emitter)) FED)	US-PGPUB; USPAT	OR	ON	2004/12/15 18:45
S15	14	("5430300").URPN.	USPAT	OR	ON	2004/12/15 17:38
S16	40	("3665241" | "3755704" | "3812559" | "3954523" | "4016017" | "4266233" | "4652467" | "4857161" | "4987101" | "5103288" | "5142184" | "5186670" | "5194780" | "5229331" | "5259799" | "5358908" | "5430300" | "5458518" | "5470801" | "5473222" | "5483067" | "5529524" | "5569058" | "5578896" | "5585301" | "5597444" | "5653619" | "5663608" | "5684356" | "5712534" | "5793154" | "5804910" | "5869169" | "5898258" | "6028322" | "6232705" | "6251470" | "6255156" | "6277765" | "6333215").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/15 17:50
S17	2	("5228878" | "5389026").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/15 18:05
S18	9	("5458518").URPN.	USPAT	OR	ON	2004/12/15 18:06
S19	9	("3755704" | "4652467" | "4940916" | "4987101" | "5103288" | "5194780" | "5225820" | "5393712" | "5430300").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/15 18:34
S20	4	(silicon with (pore porosity porous)) and (oxidat$3 oxidiz$3) and (anodiz$3 anodization) and (dielectric insulator insulat$3 isolat$3) and (((field electron) near3 (emission emissive emitting emitter)) FED)	USOCR; EPO; JPO	OR	ON	2004/12/15 18:46
S21	4	(silicon with (pore porosity porous)) and (oxidat$3 oxidiz$3) and (anodiz$3 anodization) and (dielectric insulator insulat$3 isolat$3) and (((field electron) near3 (emission emissive emitting emitter)) FED)	EPO; JPO; DERWENT	OR	ON	2004/12/15 18:46

S22	15	(silicon with (pore porosity porous)) and (oxidat$3 oxidiz$3) and (anodiz$3 anodization) and (((field electron) near3 (emission emissive emitting emitter)) FED)	EPO; JPO; DERWENT	OR	ON	2004/12/15 18:53
S23	93	(silicon with (pore porosity porous)) and (oxidat$3 oxidiz$3) and (((field electron) near3 (emission emissive emitting emitter)) FED)	EPO; JPO; DERWENT	OR	ON	2004/12/15 19:10
S24	1231	(silicon with (pore porosity porous)) and (oxidat$3 oxidiz$3) and (((field electron) near3 (emission emissive emitting emitter)) FED)	US-PGPUB; USPAT	OR	ON	2004/12/15 19:10
S25	272	((silicon with (pore porosity porous)) same (oxidat$3 oxidiz$3)) and (((field electron) near3 (emission emissive emitting emitter)) FED)	US-PGPUB; USPAT	OR	ON	2004/12/15 19:10